

BCW70 PNP EPITAXIAL SILICON TRANSISTOR**GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**

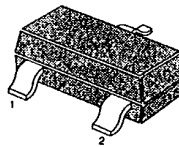
Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE0}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C=2.0\text{mA}, I_B=0$	45		V
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C=100\mu\text{A}, V_{EB}=0$	50		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=10\mu\text{A}, I_C=0$	5		V
Collector Cutoff Current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$		100	nA
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=2.0\text{mA}$	215	500	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		0.3	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=2.0\text{mA}, V_{CE}=5\text{V}$	0.6	0.75	V
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0$ $f=1.0\text{MHz}$		7.0	pF
Noise Figure	NF	$I_C=0.2\text{mA}, V_{CE}=5.0\text{V}$ $R_S=2.0\text{K}\Omega, f=1.0\text{KHz}$		10	dB

SOT-23



1. Base 2. Emitter 3. Collector

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Marking

